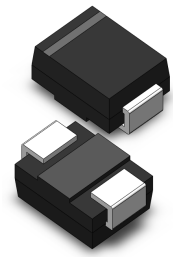
EC8FS6

SURFACE MOUNT HIGH EFFICIENCY RECTIFIER DIODES

VOLTAGE RANGE: 600V
CURRENT: 0.8A



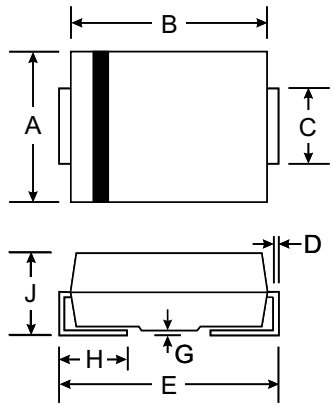
Features

- Miniature Size,Surface Mount Device
- Ultra-Fast Recove
- Low Forward Voltage Drop
- Low Power Loss, High Efficiency
- High Surge Capabilit
- Packaged in 12mm Tape and Reel
- Not RollingDuring Assembly

Mechanical Data

- Case: SMB/DO-214AA, Molded Plastic
- Terminals: Solder Plated, Solderable per MIL-STD-750, Method 2026
- Polarity: Cathode Band or Cathode Notch
- Marking: Type Number
- Weight: 0.093 grams (approx.)

RoHS COMPLIANT



SMB(DO-214AA)		
Dim	**Min**	**Max**
A	3.30	3.94
B	4.06	4.70
C	1.91	2.21
D	0.15	0.31
E	5.00	5.59
G	0.10	0.20
H	0.76	1.52
J	2.00	2.62
All Dimensions in mm		

Maximum Ratings @ T_A = 25°C unless otherwise specified

Characteristic	**Symbol**	Limits	**Unit**
RepetitivePeak Reverse Voltage	VRRM	600	V
Average Rectified Forward Current 50Hz Half Sine Wave Resistive Load Ta=25°C *1	IO	0.65	A
Average Rectified Forward Current 50Hz Half Sine Wave Resistive Load Ta=35°C *2	IO	0.8	A
R.M.S.Forward Current	IF(RMS)	1.256	A
Surge Forward Current 50Hz Half Sine Wave,Icycle,Non-repetitive	IFSM	20	A
Operating Junction Temperature Range	Tjw	-40 to +150	°C
Storage Temperature Range	Tstg	-40 to +150	°C

Electrical Characteristics @ T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min.	Typ	Max.	Unit
Peak Reverse Current Tj= 25°C, V RM = V RRM	IRM	-	-	20	μA
Peak Forward Voltage Tj= 25 °C, I FM = 0.8A	VFM	-	-	1.32	V
Reverse Recovery Time I FM =1A, -di/dt= 50A/μs, Ta = 25°C	trr	-	-	80	ns
Reverse Recovery Time I F=I R=10mA, Ta= 25°C	trr	-	-	0.4	μs
Thermal Resistance Junction to Ambient *1		-	-	157	°C /W
Thermal Resistance Junction to Ambient *2		-	-	108	°C /W